

# NGTB25N120IHLWG

## IGBT

This Insulated Gate Bipolar Transistor (IGBT) features a robust and cost effective Field Stop (FS) Trench construction, and provides superior performance in demanding switching applications, offering both low on-state voltage and minimal switching loss. The IGBT is well suited for resonant or soft switching applications. Incorporated into the device is a rugged co-packaged free wheeling diode with a low forward voltage.

### Features

- Low Saturation Voltage using Trench with Fieldstop Technology
- Low Switching Loss Reduces System Power Dissipation
- Optimized for Low Case Temperature in IH Cooker Application
- Low Gate Charge
- These are Pb-Free Devices

### Typical Applications

- Inductive Heating
- Consumer Appliances
- Soft Switching

### ABSOLUTE MAXIMUM RATINGS

| Rating                                                                             | Symbol           | Value           | Unit             |
|------------------------------------------------------------------------------------|------------------|-----------------|------------------|
| Collector-emitter voltage                                                          | $V_{CES}$        | 1200            | V                |
| Collector current<br>@ $T_C = 25^\circ\text{C}$<br>@ $T_C = 100^\circ\text{C}$     | $I_C$            | 50<br>25        | A                |
| Pulsed collector current, $T_{\text{pulse}}$ limited by $T_{J\text{max}}$          | $I_{CM}$         | 200             | A                |
| Diode forward current<br>@ $T_C = 25^\circ\text{C}$<br>@ $T_C = 100^\circ\text{C}$ | $I_F$            | 50<br>25        | A                |
| Diode pulsed current, $T_{\text{pulse}}$ limited by $T_{J\text{max}}$              | $I_{FM}$         | 200             | A                |
| Gate-emitter voltage                                                               | $V_{GE}$         | $\pm 20$        | V                |
| Power Dissipation<br>@ $T_C = 25^\circ\text{C}$<br>@ $T_C = 100^\circ\text{C}$     | $P_D$            | 192<br>77       | W                |
| Operating junction temperature range                                               | $T_J$            | $-55$ to $+150$ | $^\circ\text{C}$ |
| Storage temperature range                                                          | $T_{\text{stg}}$ | $-55$ to $+150$ | $^\circ\text{C}$ |
| Lead temperature for soldering, 1/8" from case for 5 seconds                       | $T_{\text{SLD}}$ | 260             | $^\circ\text{C}$ |

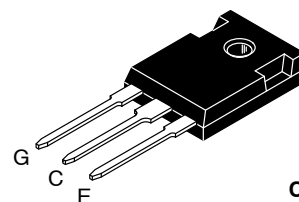
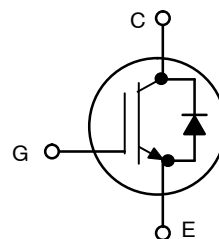
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



ON Semiconductor®

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25 A, 1200 V  
 $V_{CEsat} = 1.85 \text{ V}$   
 $E_{off} = 0.8 \text{ mJ}$



TO-247  
CASE 340L  
STYLE 4

### MARKING DIAGRAM



A = Assembly Location  
Y = Year  
WW = Work Week  
G = Pb-Free Package

### ORDERING INFORMATION

| Device          | Package             | Shipping        |
|-----------------|---------------------|-----------------|
| NGTB25N120IHLWG | TO-247<br>(Pb-Free) | 30 Units / Rail |

# NGTB25N120IHLWG

## THERMAL CHARACTERISTICS

| Rating                                         | Symbol          | Value | Unit                 |
|------------------------------------------------|-----------------|-------|----------------------|
| Thermal resistance junction-to-case, for IGBT  | $R_{\theta JC}$ | 0.65  | $^{\circ}\text{C/W}$ |
| Thermal resistance junction-to-case, for Diode | $R_{\theta JC}$ | 2.0   | $^{\circ}\text{C/W}$ |
| Thermal resistance junction-to-ambient         | $R_{\theta JA}$ | 40    | $^{\circ}\text{C/W}$ |

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^{\circ}\text{C}$ unless otherwise specified)

| Parameter | Test Conditions | Symbol | Min | Typ | Max | Unit |
|-----------|-----------------|--------|-----|-----|-----|------|
|-----------|-----------------|--------|-----|-----|-----|------|

### STATIC CHARACTERISTIC

|                                                                   |                                                                                                                           |               |        |             |            |    |
|-------------------------------------------------------------------|---------------------------------------------------------------------------------------------------------------------------|---------------|--------|-------------|------------|----|
| Collector-emitter breakdown voltage, gate-emitter short-circuited | $V_{GE} = 0\text{ V}, I_C = 500\text{ }\mu\text{A}$                                                                       | $V_{(BR)CES}$ | 1200   | –           | –          | V  |
| Collector-emitter saturation voltage                              | $V_{GE} = 15\text{ V}, I_C = 25\text{ A}$<br>$V_{GE} = 15\text{ V}, I_C = 25\text{ A}, T_J = 150^{\circ}\text{C}$         | $V_{CEsat}$   | –<br>– | 1.85<br>2.1 | 2.3<br>–   | V  |
| Gate-emitter threshold voltage                                    | $V_{GE} = V_{CE}, I_C = 250\text{ }\mu\text{A}$                                                                           | $V_{GE(th)}$  | 4.5    | 5.5         | 6.5        | V  |
| Collector-emitter cut-off current, gate-emitter short-circuited   | $V_{GE} = 0\text{ V}, V_{CE} = 1200\text{ V}$<br>$V_{GE} = 0\text{ V}, V_{CE} = 1200\text{ V}, T_J = 150^{\circ}\text{C}$ | $I_{CES}$     | –<br>– | –<br>–      | 0.5<br>2.0 | mA |
| Gate leakage current, collector-emitter short-circuited           | $V_{GE} = 20\text{ V}, V_{CE} = 0\text{ V}$                                                                               | $I_{GES}$     | –      | –           | 100        | nA |

### DYNAMIC CHARACTERISTIC

|                              |                                                                  |           |   |      |   |    |
|------------------------------|------------------------------------------------------------------|-----------|---|------|---|----|
| Input capacitance            | $V_{CE} = 20\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$    | $C_{ies}$ | – | 4700 | – | pF |
| Output capacitance           |                                                                  | $C_{oes}$ | – | 155  | – |    |
| Reverse transfer capacitance |                                                                  | $C_{res}$ | – | 100  | – |    |
| Gate charge total            | $V_{CE} = 600\text{ V}, I_C = 25\text{ A}, V_{GE} = 15\text{ V}$ | $Q_g$     |   | 200  |   | nC |
| Gate to emitter charge       |                                                                  | $Q_{ge}$  |   | 38   |   |    |
| Gate to collector charge     |                                                                  | $Q_{gc}$  |   | 100  |   |    |

### SWITCHING CHARACTERISTIC, INDUCTIVE LOAD

|                         |                                                                                                                                            |              |  |     |  |    |
|-------------------------|--------------------------------------------------------------------------------------------------------------------------------------------|--------------|--|-----|--|----|
| Turn-off delay time     | $T_J = 25^{\circ}\text{C}$<br>$V_{CC} = 600\text{ V}, I_C = 25\text{ A}$<br>$R_g = 10\text{ }\Omega$<br>$V_{GE} = 0\text{ V}/15\text{ V}$  | $t_{d(off)}$ |  | 235 |  | ns |
| Fall time               |                                                                                                                                            | $t_f$        |  | 160 |  |    |
| Turn-off switching loss |                                                                                                                                            | $E_{off}$    |  | 0.8 |  | mJ |
| Turn-off delay time     | $T_J = 125^{\circ}\text{C}$<br>$V_{CC} = 600\text{ V}, I_C = 25\text{ A}$<br>$R_g = 10\text{ }\Omega$<br>$V_{GE} = 0\text{ V}/15\text{ V}$ | $t_{d(off)}$ |  | 250 |  | ns |
| Fall time               |                                                                                                                                            | $t_f$        |  | 225 |  |    |
| Turn-off switching loss |                                                                                                                                            | $E_{off}$    |  | 1.9 |  | mJ |

### DIODE CHARACTERISTIC

|                 |                                                                                                                 |       |  |            |     |   |
|-----------------|-----------------------------------------------------------------------------------------------------------------|-------|--|------------|-----|---|
| Forward voltage | $V_{GE} = 0\text{ V}, I_F = 25\text{ A}$<br>$V_{GE} = 0\text{ V}, I_F = 25\text{ A}, T_J = 150^{\circ}\text{C}$ | $V_F$ |  | 1.7<br>1.8 | 1.8 | V |
|-----------------|-----------------------------------------------------------------------------------------------------------------|-------|--|------------|-----|---|

TYPICAL CHARACTERISTICS

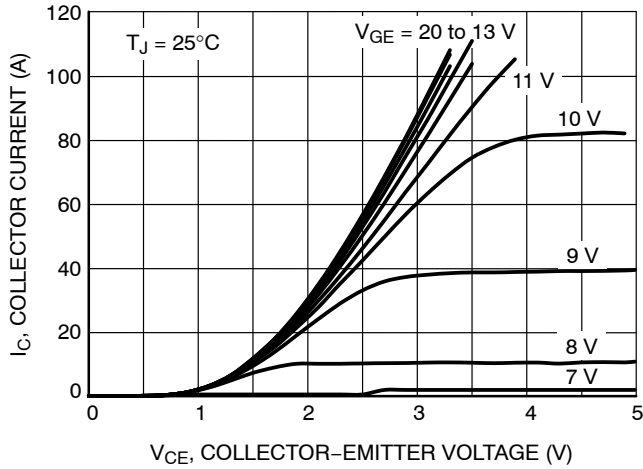


Figure 1. Output Characteristics

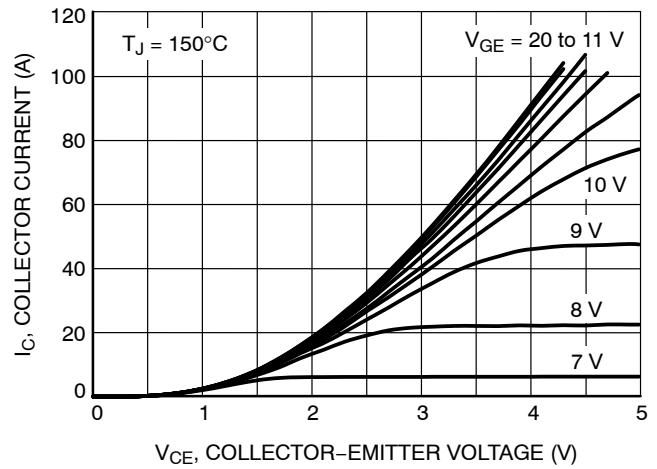


Figure 2. Output Characteristics

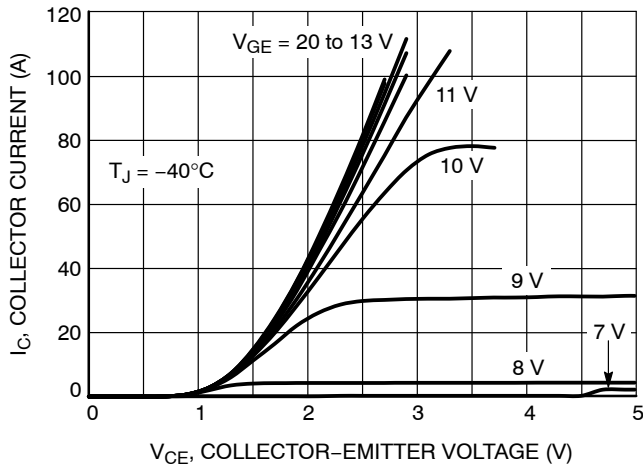


Figure 3. Output Characteristics

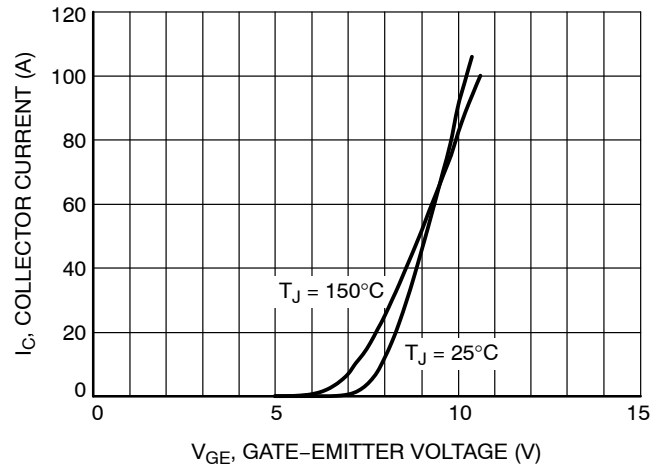


Figure 4. Typical Transfer Characteristics

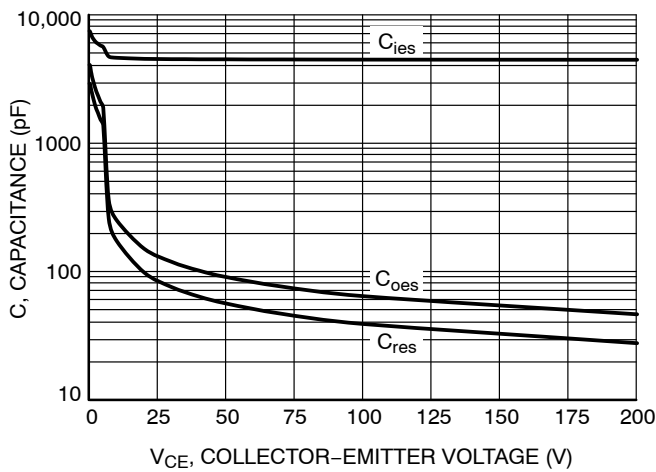


Figure 5. Typical Capacitance

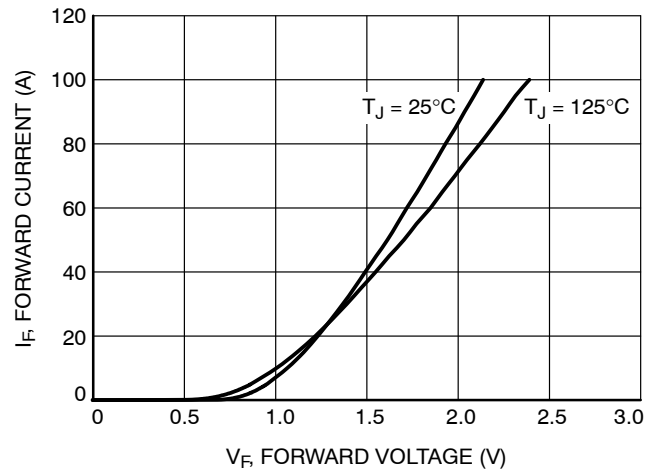


Figure 6. Diode Forward Characteristics

# NGTB25N120IHLWG

## TYPICAL CHARACTERISTICS

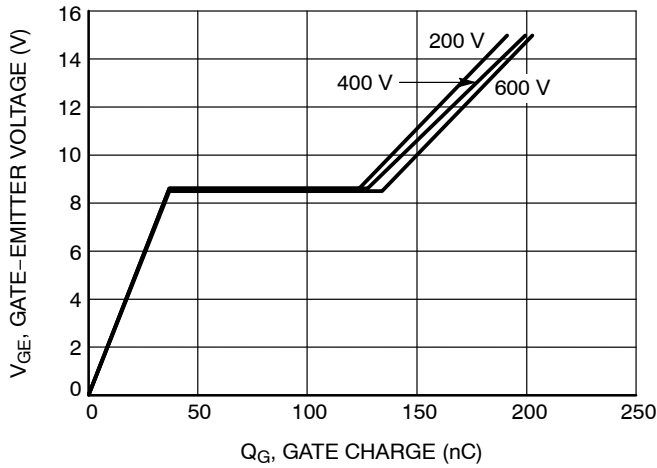


Figure 7. Typical Gate Charge

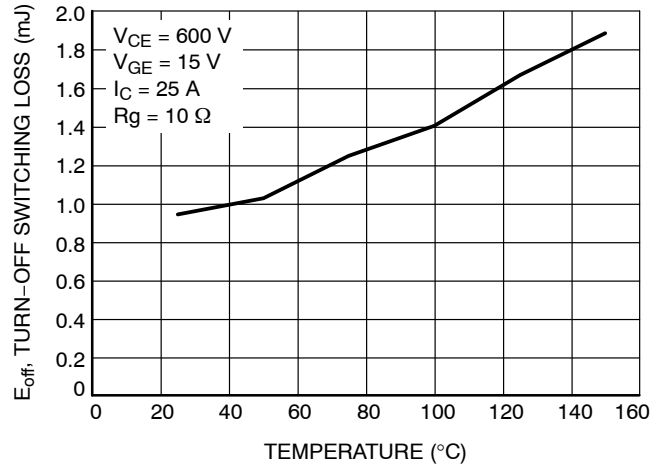


Figure 8. Energy Loss vs. Temperature

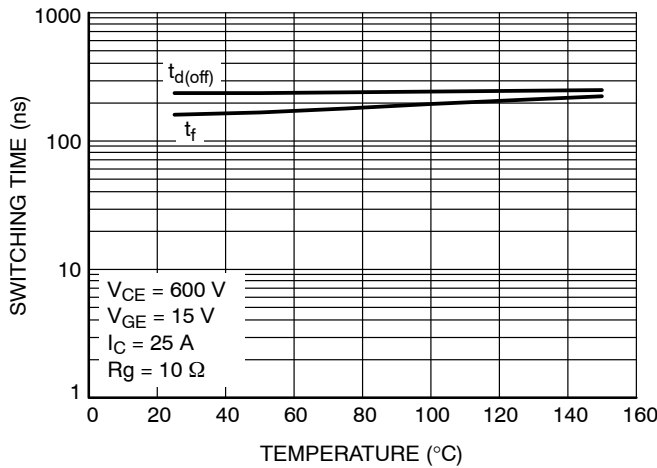


Figure 9. Switching Time vs. Temperature

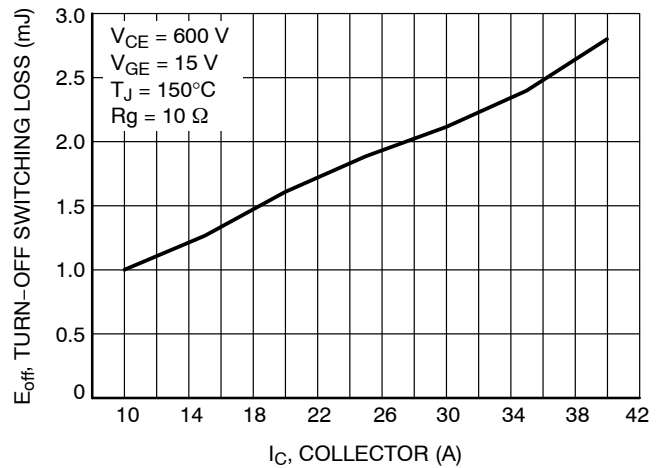


Figure 10. Energy Loss vs.  $I_C$

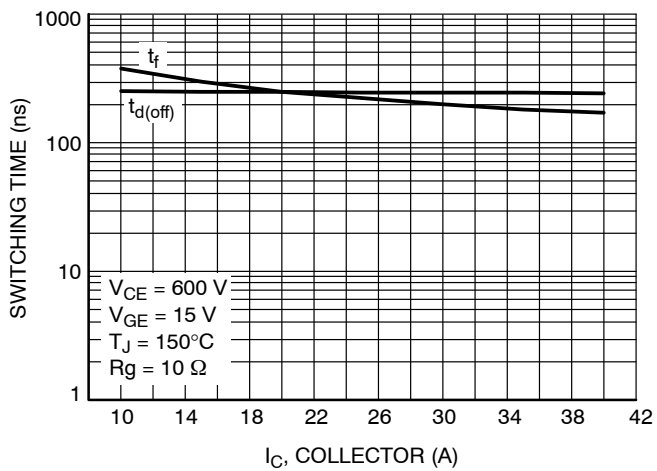


Figure 11. Switching Time vs.  $I_C$

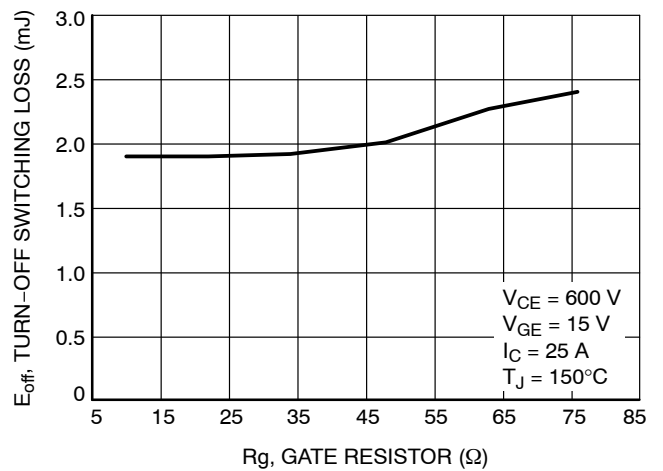


Figure 12. Energy Loss vs.  $R_g$

# NGTB25N120IHLWG

## TYPICAL CHARACTERISTICS

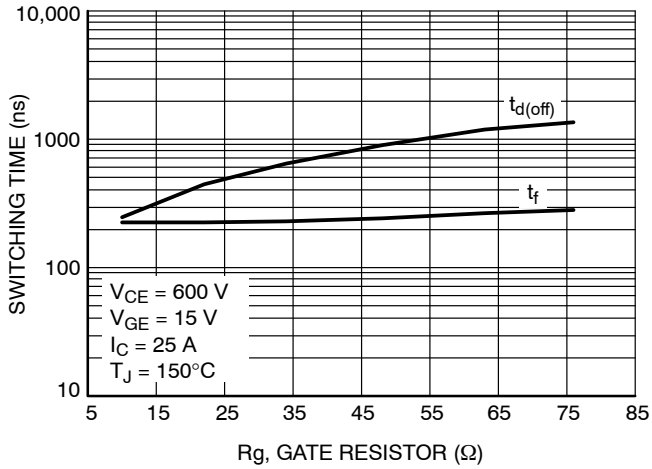


Figure 13. Switching Time vs.  $R_g$

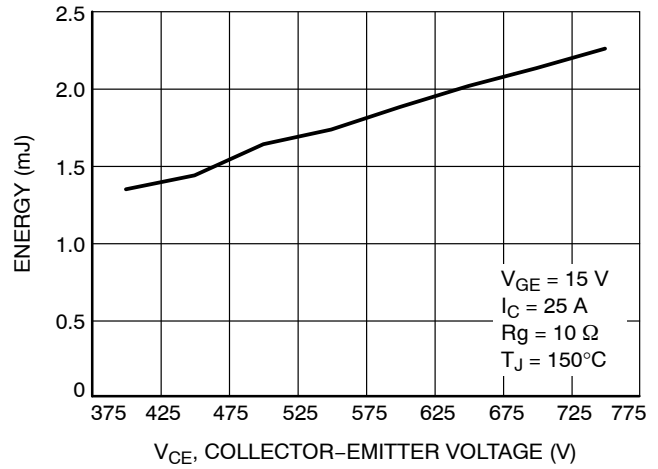


Figure 14. Energy Loss vs.  $V_{CE}$

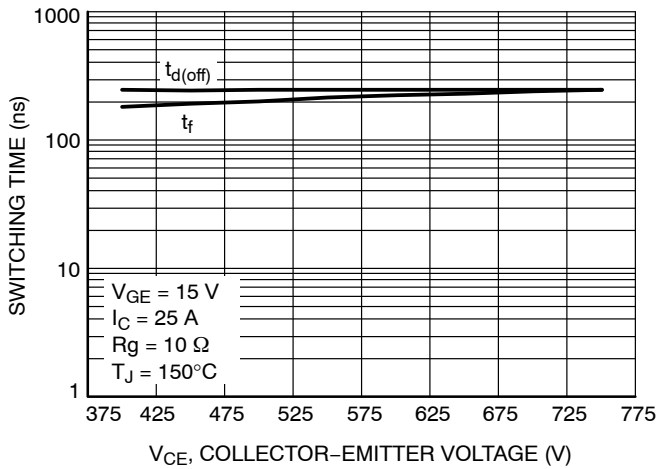


Figure 15. Switching Time vs.  $V_{CE}$

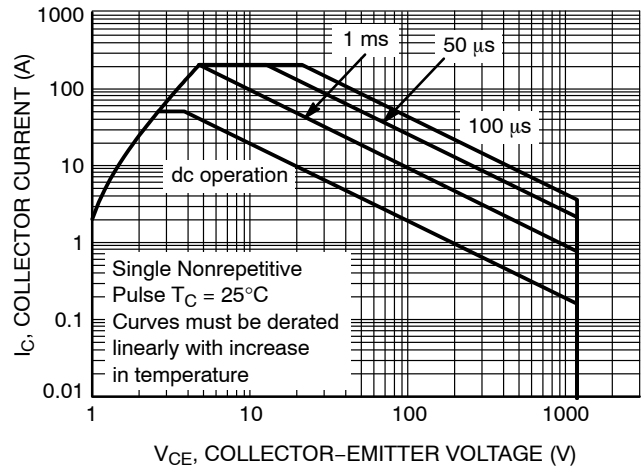


Figure 16. Safe Operating Area

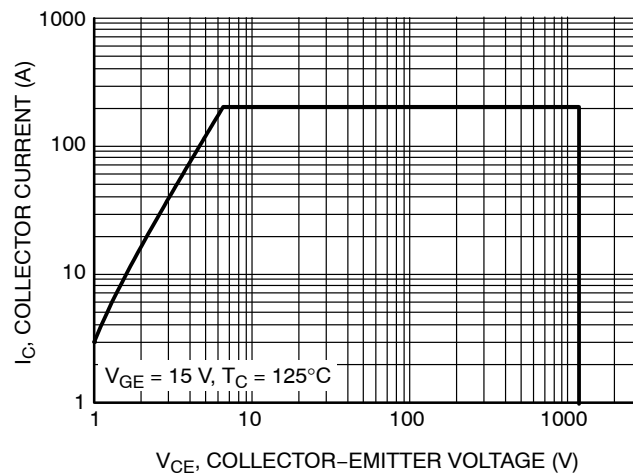


Figure 17. Reverse Bias Safe Operating Area

# NGTB25N120HLWG

## TYPICAL CHARACTERISTICS

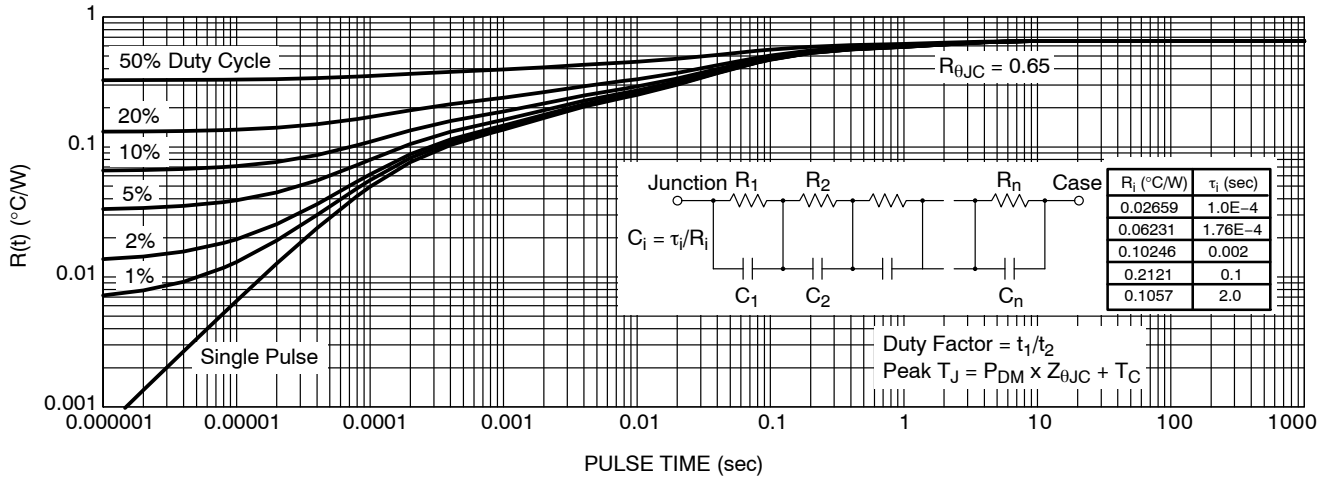


Figure 18. IGBT Transient Thermal Impedance

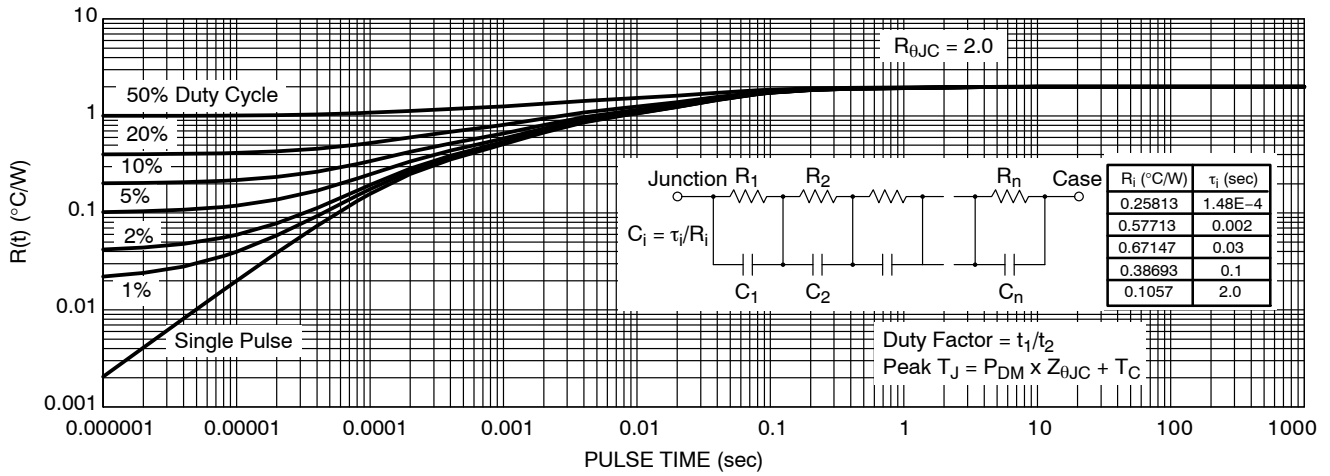


Figure 19. Diode Transient Thermal Impedance

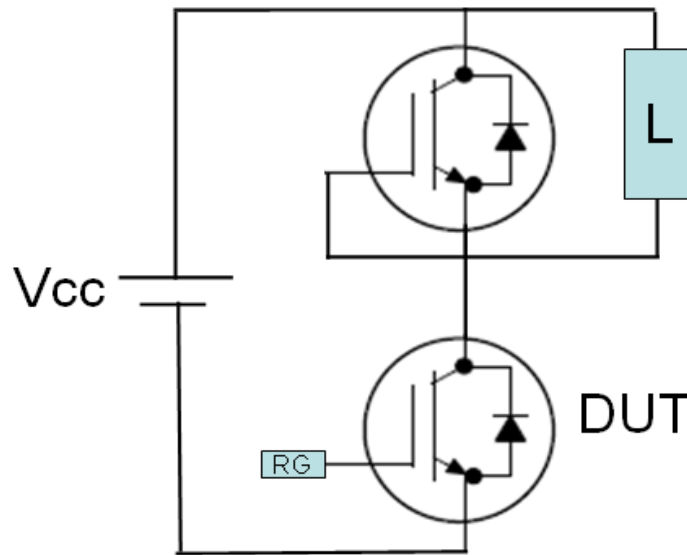


Figure 20. Test Circuit for Switching Characteristics

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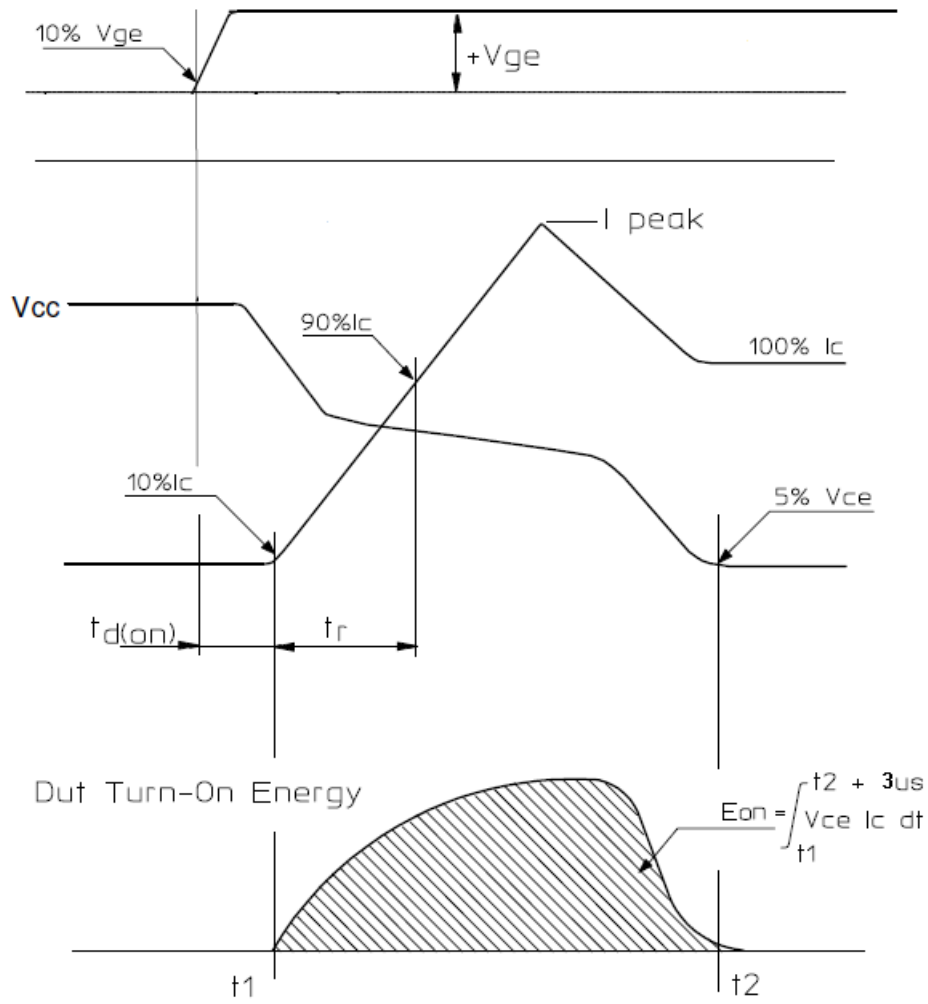


Figure 21. Definition of Turn On Waveform

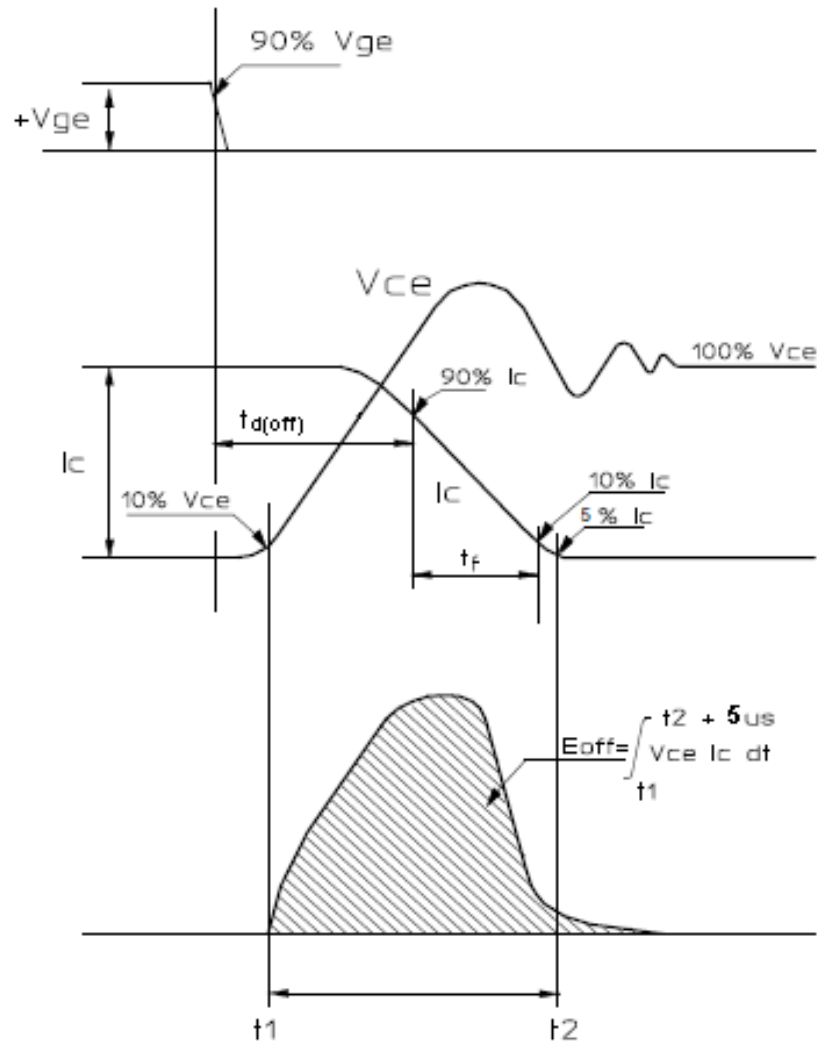
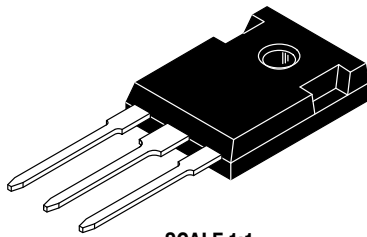


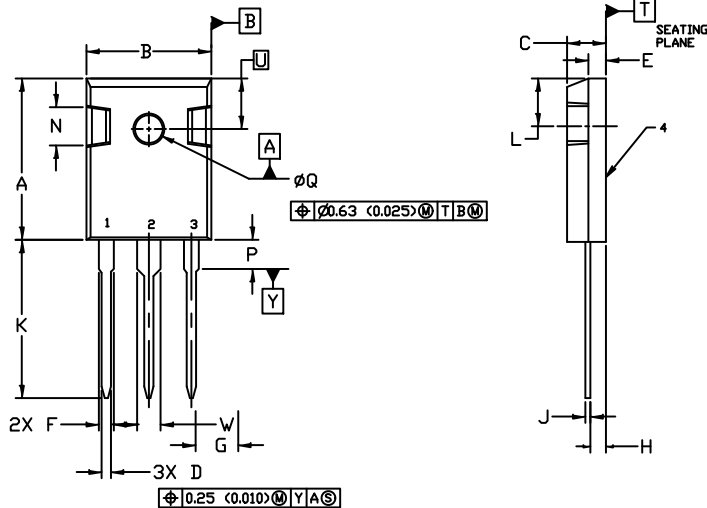
Figure 22. Definition of Turn Off Waveform



TO-247  
CASE 340L  
ISSUE G

DATE 06 OCT 2021

SCALE 1:1

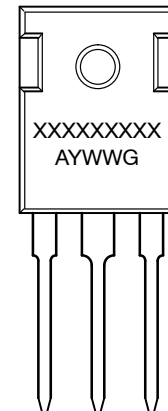


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER

| DIM | MILLIMETERS |       | INCHES    |       |
|-----|-------------|-------|-----------|-------|
|     | MIN.        | MAX.  | MIN.      | MAX.  |
| A   | 20.32       | 21.08 | 0.800     | 0.830 |
| B   | 15.75       | 16.26 | 0.620     | 0.640 |
| C   | 4.70        | 5.30  | 0.185     | 0.209 |
| D   | 1.00        | 1.40  | 0.040     | 0.055 |
| E   | 1.90        | 2.60  | 0.075     | 0.102 |
| F   | 1.65        | 2.13  | 0.065     | 0.084 |
| G   | 5.45 BSC    |       | 0.215 BSC |       |
| H   | 1.50        | 2.49  | 0.059     | 0.098 |
| J   | 0.40        | 0.80  | 0.016     | 0.031 |
| K   | 19.81       | 20.83 | 0.780     | 0.820 |
| L   | 5.40        | 6.20  | 0.212     | 0.244 |
| N   | 4.32        | 5.49  | 0.170     | 0.216 |
| P   | ----        | 4.50  | ----      | 0.177 |
| Q   | 3.55        | 3.65  | 0.140     | 0.144 |
| U   | 6.15 BSC    |       | 0.242 BSC |       |
| W   | 2.87        | 3.12  | 0.113     | 0.123 |

GENERIC  
MARKING DIAGRAM\*



- STYLE 1:  
PIN 1. GATE  
2. DRAIN  
3. SOURCE  
4. DRAIN
- STYLE 2:  
PIN 1. ANODE  
2. CATHODE (S)  
3. ANODE 2  
4. CATHODE (S)
- STYLE 3:  
PIN 1. BASE  
2. COLLECTOR  
3. EMITTER  
4. COLLECTOR
- STYLE 4:  
PIN 1. GATE  
2. COLLECTOR  
3. EMITTER  
4. COLLECTOR
- STYLE 5:  
PIN 1. CATHODE  
2. ANODE  
3. GATE  
4. ANODE
- STYLE 6:  
PIN 1. MAIN TERMINAL 1  
2. MAIN TERMINAL 2  
3. GATE  
4. MAIN TERMINAL 2

XXXXX = Specific Device Code  
A = Assembly Location  
Y = Year  
WW = Work Week  
G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

|                  |             |                                                                                                                                                                                  |
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